

RED DIODE LASER AT 650/655nm

RN-III-650R/655R/1~200mW



It features integrated electronics, plug and play, miniaturization,

international standard interface. They are the ideal solution for a wide

range of applications including life sciences, environmental monitoring,

inspection and machine vision.



RN-III-650R/655R/1~200mW			
Central wavelength (nm)		650+13/-5	655±10
Operating mode		CW	
Output power (mW)		>1,10,20,, 180	
Power stability (rms, over 4 hours)		<1%, <2%, <3% (<0.5%, optional)	
Transverse mode		Near TEM ₀₀	
M ² factor		<1.5 (<1.2, optional)	
Beam diameter at the aperture (mm)		~3.0 (~1.2, optional)	
Beam divergence, full angle (mrad)		<1.0	
Polarization ratio		>50:1 (>100:1, optional) Horizontal±5 degree (Vertical Optional)	
Warm-up time (minutes)		<5	
Pointing stability after warm-up (mrad)		<0.05	
Beam height from base plate (mm)		24. 8	
Operating temperature (°C)		10~35	
Power supply	85-264VAC	PSU-III-LED/ PSU-III-FDA (Frequency for 1Hz-30kHz)	
	100-240VAC	PSU-A-D (Frequency for 30kHz -100kHz)	
TTL / Analog modulation		TTL or Analog with 1Hz-1kHz 1kHz-10kHz, 10kHz-30kHz, 30kHz-100kHz optional	
Expected lifetime (hours)		10000	
Warranty		1 year	

北京市昌平区 国家信息产业基地立业路13号2011 ≤ sales@ranbond.com